

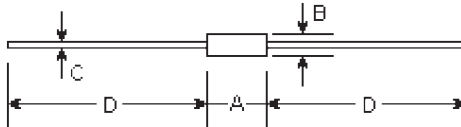
### Features

**Silicon Epitaxial Planar Diodes**  
for general purpose and switching

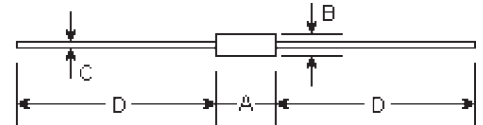
### DO-35

The types 1N4149, 1N4447 and 1N4449 are also available in glass case DO-34.

### DO-34



DIM	DIMENSIONS				Note
	inches		mm		
	Min.	Max.	Min.	Max.	
A	-	0.114	-	2.9	
B	-	0.075	-	1.9	φ
C	-	0.017	-	0.42	φ
D	0.830	-	16.0	-	



DIM	DIMENSIONS				Note
	inches		mm		
	Min.	Max.	Min.	Max.	
A	-	0.154	-	3.9	
B	-	0.075	-	1.9	φ
C	-	0.020	-	0.52	φ
D	1.083	-	27.50	-	

### Electrical Characteristics

Type	Peak reverse voltage	Max. aver. rectified current	Max. power dissip. at 25°C	Max. junction temperature	Max. forward voltage drop		Max. reverse current		Max. reverse recovery time	
	$V_{RM}$ V	$I_O$ mA	$P_{tot}$ mW	$T_J$ °C	$V_F$ V	at $I_F$ mA	$I_n$ nA	at $V_R$ V	$t_{tr}$ nS	Conditions
1N914	100	75	500	200	1.0	10	25	20	Max. 4.0	$I_F=10\text{mA}$ , $V_R=6\text{V}$ , $R_{\theta L}=100\ \Omega$ , to $I_R=1\text{mA}$
1N4149 <sup>(1)</sup>	100	150	500	200	1.0	10	25	20	Max. 4.0	$I_F=10\text{mA}$ , $V_R=6\text{V}$ , $R_{\theta L}=100\ \Omega$ , to $I_R=1\text{mA}$
1N4150	50	200	500	200	1.0	200	100	50	Max. 4.0	$I_F=I_R=10$ to 200 mA, to 0.1 $I_F$
1N4152	40	150	400	175	0.55	0.10	50	30	Max. 2.0	$I_F=10\text{mA}$ , $V_R=6\text{V}$ , $R_{\theta L}=100\ \Omega$ , to $I_R=1\text{mA}$
1N4153	75	150	400	175	0.55	0.10	50	50	Max. 2.0	$I_F=10\text{mA}$ , $V_R=6\text{V}$ , $R_{\theta L}=100\ \Omega$ , to $I_R=1\text{mA}$
1N4154	35	150 <sup>(2)</sup>	500	200	1.0	0.10	100	25	Max. 2.0	$I_F=10\text{mA}$ , $V_R=6\text{V}$ , $R_{\theta L}=100\ \Omega$ , to $I_R=1\text{mA}$
1N4447 <sup>(1)</sup>	100	150	500	200	1.0	20	25	20	Max. 4.0	$I_F=10\text{mA}$ , $V_R=6\text{V}$ , $R_{\theta L}=100\ \Omega$ , to $I_R=1\text{mA}$
1N4449 <sup>(1)</sup>	100	150	500	200	1.0	30	25	20	Max. 4.0	$I_F=10\text{mA}$ , $V_R=6\text{V}$ , $R_{\theta L}=100\ \Omega$ , to $I_R=1\text{mA}$
1N4450	40	150	400	175	0.54	0.50	50	30	Max. 4.0	$I_F=I_R=10\text{mA}$ , to $I_R=1\text{mA}$
1N4451	40	150	400	175	0.50	0.10	50	30	Max. 10	$I_F=I_R=10\text{mA}$ , to $I_R=1\text{mA}$
1N4453	30	150	400	175	0.55	0.01	50	20	-	-
1N4454	75	150	400	175	1.0	10	100	50	Max. 4.0	$I_F=I_R=10\text{mA}$ , to $I_R=1\text{mA}$

Notes:

- (1) These diodes are also available in glass case DO-34
- (2) Valid provided that leads at a distance of 8 mm from case are kept at ambient temperature

Parameters for diodes in case DO-34:  $P_{tot}=300\text{mW}$   $T_S=-65$  to  $+175^\circ\text{C}$   
 $T_J=175^\circ\text{C}$   $R_{\theta ha} \leq 0.4\text{K/mW}$